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Schmidt et al.

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(54) **METHOD FOR MANUFACTURING A SOLAR CELL WITH A SURFACE-PASSIVATING DIELECTRIC DOUBLE LAYER, AND CORRESPONDING SOLAR CELL**

(58) **Field of Classification Search**
CPC H01L 31/00; H01L 27/00; H01L 31/0256;
H01L 31/18; H01L 31/02168
(Continued)

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(57) **ABSTRACT**

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(Continued)

A solar cell with a dielectric double layer and also a method for the manufacture thereof are described. A first dielectric layer (3), which contains aluminum oxide or consists of aluminum oxide, and a second, hydrogen-containing dielectric layer (5) are produced by means of atomic layer deposition, allowing very good passivation of the surface of solar cells to be achieved.

(52) **U.S. Cl.**
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16 Claims, 1 Drawing Sheet

